

SANYO

No. 4354

FDD Spindle Motor Driver

Overview

The LB1890M is a 3-phase DD motor driver IC and is an ideal FDD spindle motor driver for 3.5 inch applications.

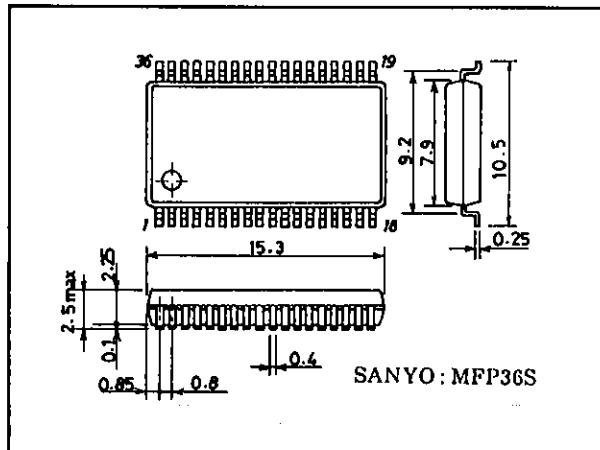
Functions and Features

- Three phase total wave linear driver
- Eliminates need for output electrolytic capacitor (however, depending on the motor, this may not apply)
- On-chip digital speed control
- Start/stop circuit
- Current limiter circuit
- On-chip index comparator (single HYS)
- On-chip index delay circuit
- AGC circuit
- Temperature protection circuit

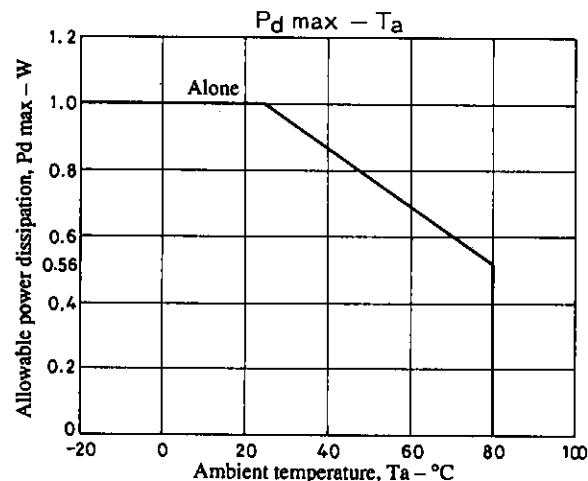
Package Dimensions

unit : mm

3129-MFP36S



Allowable power dissipation vs. ambient temperature



Pin Assignment

sub GND	[1]	36	POW GND
VOUT	[2]	35	UOUT
WOUT	[3]	34	Rf
AGC	[4]	33	VCC
WIN-	[5]	32	VID
WIN+	[6]	31	IAO
VIN-	[7]	30	IAI
VIN+	[8]	29	DO
UIN-	[9]	28	S/S2
UIN+	[10]	27	S/S1
HB	[11]	26	FG+
FC	[12]	25	FG-
I+	[13]	24	FG0
I-	[14]	23	DT0
SL	[15]	22	DT2
NC	[16]	21	DT1
X1	[17]	20	ID
X2	[18]	19	GND

LB 1890M

[Top View]

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20593TS A8-9675, 9414 No.4354-1/8

Specifications

Absolute Maximum Ratings at Ta = 25°C

				unit
Maximum supply voltage	V _{CC} max		7.0	V
Maximum output current	I _O max1	t≤0.5sec	1.0	A
Steady Maximum output current	I _O max2		0.7	A
Allowable power dissipation	P _d max	IC alone	1	W
Operating temperature	T _{OPR}		-20 to +80	°C
Storage temperature range	T _{SIG}		-40 to +150	°C

Allowable Operating Conditions at Ta = 25°C

Supply voltage	V _{CC}	4.2 to 6.5	unit
		V	

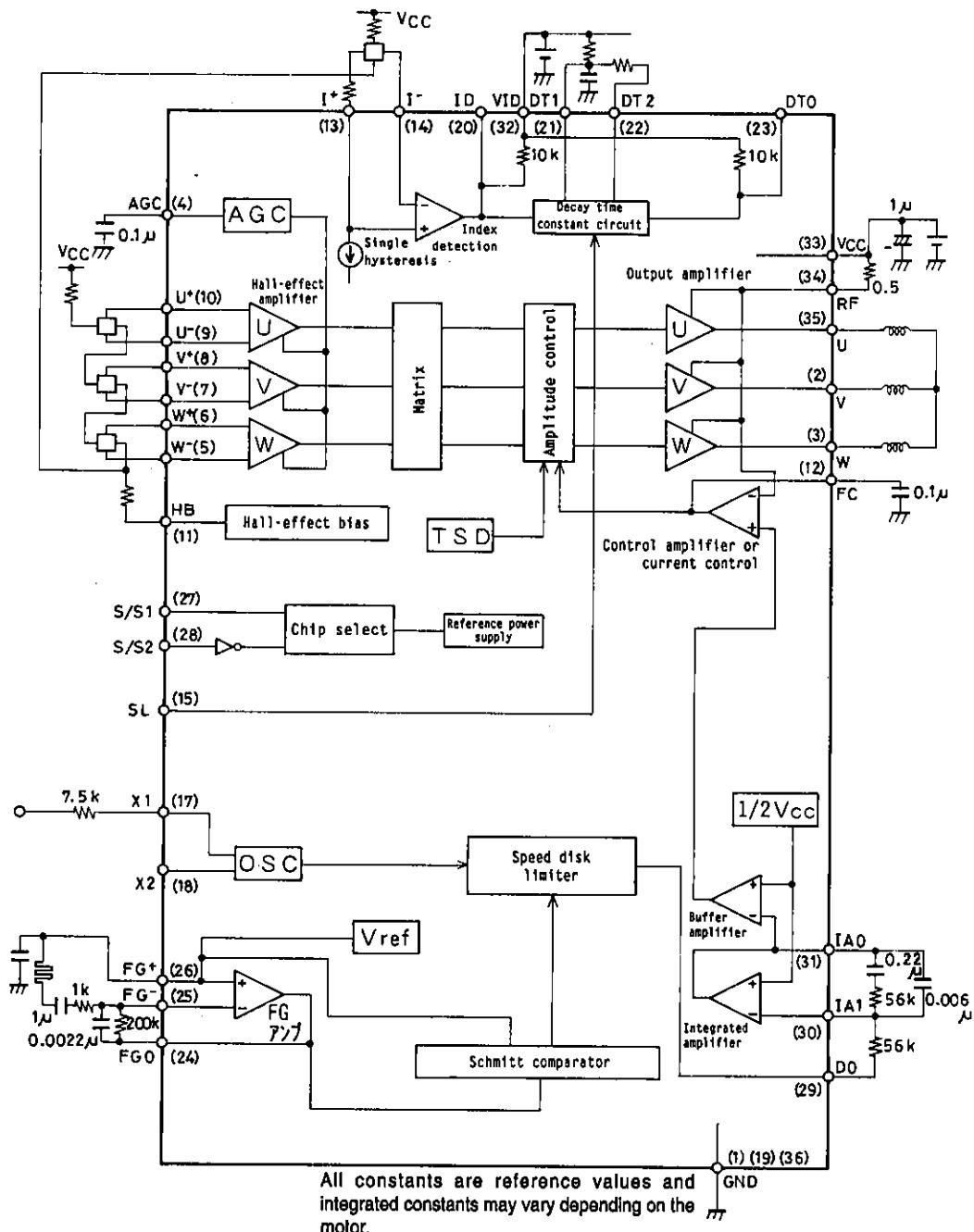
Electrical Characteristics at Ta = 25°C, V_{CC} = 5V

Current consumption	I _{CC01}	V _{CC} = 5.0V (Stop)	min	typ	max	unit	note
	I _{CC1}	V _{CC} = 5.0V (Steady)		20	30	mA	
Time changeover bias current	I _{SL}				0.4	mA	
Time changeover input voltage 1	V _{SLL}	0			0.8	V	
Time changeover input voltage 2	V _{SLH}	2.0			V _{CC}	V	
S/S1 bias current	I _{S/S1}				0.4	mA	
S/S1 start voltage	V _{S/S1}	2.0			V _{CC}	V	
S/S1 stop voltage	V _{S/S1}	0			0.8	V	
S/S2 bias current	I _{S/S2}				0.1	mA	
S/S2 start voltage	V _{S/S2}	0			0.8	V	
S/S2 stop voltage	V _{S/S2}	2.0			V _{CC}	V	
Hall-effect bias amplifier input current	I _{HB}				20	μA	
In-phase input voltage range	V _h	2.2	V _{CC} - 0.7		V		
Differential input voltage range	V _{dif}	70	250	mVp-p	*2		
Input offset voltage	V _{ho}		±1.0	mV	*1		
Hall-Effect output voltage	V _H	I _H = 5mA	1.5	1.8	V		
Leak current	I _{HL}	Stop		±10	μA		
Output saturation voltage	V _{sat1}	I _O = 0.35A, V _{CC} = 4.2V	1.2	1.4	V		
Sink plus source	V _{sat2}	I _O = 0.70A, V _{CC} = 4.2V	1.5	2.0	V		
Output leak current	I _{OL}			±1.0	mA		
Current limiter	V _{ref1}		0.27	0.30	0.33	V	
Control amplifier voltage gain	G _C			-6	dB		
Voltage gain phase differential	ΔG _C			±1	dB		
Integrated amplifier internal reference voltage	V _{ref2}		V _{CC} /2		V		
Integrated amplifier bias current	I _{ib}			±1	μA		
Integrated output voltage amplitude	V _{i+}	II = -0.5 mA with reference of V _{ref2}	0.75		V		
	V _{i-}	II = 0.5 mA with reference of V _{ref2}	-1.4		V		
Gain band width			1000		kHz	*1	
FG amplifier input voltage	V _{FG}		5		100	mVp-p	
FG amplifier voltage gain	G _{FG}	Open loop		60		dB	*1
FG amplifier input offset	V _{FG0}				±10	mV	
FG amplifier internal reference voltage	V _{FBG}		2.20	2.50	2.80	V	
Schmitt hysteresis width	△V _{sh1}	"H" → "L"		25		mV	*1
	△V _{sh2}	"L" → "H"		25		mV	*1
Schmitt input operation level	V _{sh}		1	V _{CC} -1	V		
Speed disk recount number	N		992				
Disk recount out "L" level voltage	V _{DL}	I _D = -0.5mA			0.3	V	
Disk recount out "H" level voltage	V _{DH}	I _D = 0.5mA	V _{CC} -0.4		V		
Disk recount out leak current	I _{DI}				±1.0	μA	
Disk recount operation frequency	F _D				1.0	MHz	*1
Oscillation range	F _{OSC}				1.0	MHz	*1
Index bias current	I _{IDB}				±10	μA	
In-phase input voltage range	V _{ID}		1.5	V _{CC} -0.5	V		
Hysteresis setting current range	I _{ID0}		5	10	15	μA	
Index output "L" level voltage	V _{IDL}	V _{ID} = 5V			0.4	V	
Index output "H" level voltage	V _{IDH}	V _{ID} = 5V	4.5		V		
Break-down voltage	V _{DLDC}	V _{ID} = 5V		2.50	V		
Delay output "L" level voltage	V _{DLL}	V _{ID} = 5V			0.4	V	
Delay output "H" level voltage	V _{D LH}	V _{ID} = 5V	4.5		V		
Excessive heat protected operating temperature	T _{SD}		150	180	°C	*1	
Hysteresis width	△T _{SD}			40	°C	*1	

Note: *1) Marked values (*1) are guaranteed by the design itself and therefore do not require measurement.

*2) When hall-effect input becomes larger, kick-back occurs to the output waveform and for this reason, 200 m Vp-p or less is recommended.

Block Diagram



Pin Description

Unit (resistance: Ω)

Pin Number	Pin Symbol	Pin Voltage	Equivalent Circuit	Pin Description
5	W-	2.2V min		• W-phase hall-effect input pin.
6	W+	V _{CC} - 0.7V max		W+ > W- is established when logic is at an "H" level.
7	V-			• V-phase hall-effect input pin.
8	V+			V+ > V- is established when logic is at an "H" level.
9	U-			• U-phase hall-effect input pin.
10	U+			U+ > U- is established when logic is at an "H" level.
11	HB	1.5V typ (I _H = 5mA)		• Minus pin for hall-effect bias. When stopped, switches open and hall-effect bias severs.
12	FC			• Frequency characteristics revision pin By installing a capacitor between this pin and GND, close-loop oscillation for the current control system halts.
13	I ⁺	1.5V min		• Index input pin.
14	I ⁻	V _{CC} - 0.5V max		When the I ⁺ pin is at an "L" level, I ₁ operates with the fixed current of I ₁ = 10 μ A and when at an "H" level, I ₁ does not flow. Hysteresis width is determined by the resistor attached externally to the I ⁺ pin.
15	SL	"L": 0.8V max "H": 2.0V min		• Time changeover pin. 1 : 1.2 "L" level : "H" level
17	X1			• Reference clock generating pin.
18	X2			
19	GND			• Ground pin. Grounded as with pins 1 and 36.

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Unit (resistance: Ω)

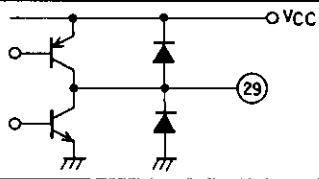
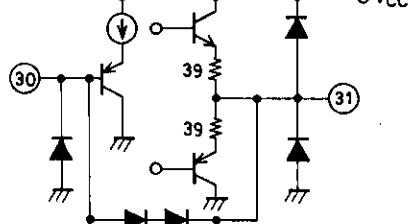
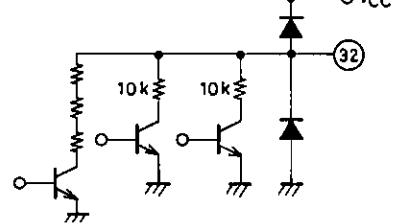
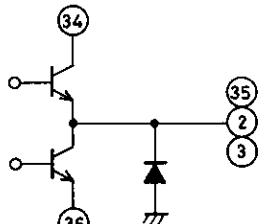
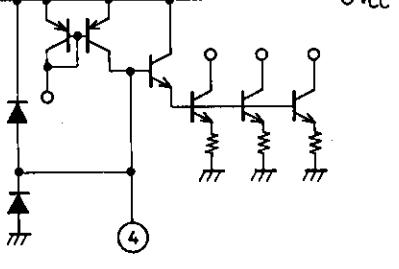
Pin Number	Pin Symbol	Pin Voltage	Equivalent Circuit	Pin Description
20	ID	"L": 0.4V max "H": 4.5V min (When V_{ID} equals 5 V)		• Index pulse output pin.
21	DT1			• Pin connecting the external CR for the delay time constant circuit.
22	DT2			• Break-down current setting pin for the delay time constant circuit.
23	DTO	"L": 0.4V max "H": 4.5V min (When V_{ID} equals 5 V)		• Index delay pulse output pin.
24	FG0			• FG amplifier output pin.
25	FG-			• FG amplifier negative input pin.
26	FG+	2.48V (When V_{ID} equals 5 V)		• FG amplifier positive input pin. Generates reference voltage within IC.
27	S/S1	"L": 0.8V max "H": 2.0V min		• Start/stop changeover pin. "H" level active.
28	S/S2	"L": 0.8V max "H": 2.0V min		• Start/stop changeover pin. "L" level active.

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Unit (resistance: Ω).

Pin Number	Pin Symbol	Pin Voltage	Equivalent Circuit	Pin Description
29	DO			• Speed discriminator output pin.
30	IAI			• Integrated amplifier input pin.
31	IAO			• Integrated amplifier output pin.
32	V _{ID}			• Index pulse output and index delay pulse output power supply pin. For applications when V _{CC} equals 5 V, V _{CC} = V _{ID} = 5 V.
33	V _{CC}			• Total power supply voltage pin except for V _{ID} . Voltage must be stable and free of ripple and noise interference.
34	R _I			• Output current detection pin. By installing an R _I resistor between this pin and V _{CC} , output current is detected as voltage. Voltage detection at this pin activates the current limiter.
35	U _{OUT}			• U-phase output pin.
36	Pow GND			• Output transistor ground pin.
1	Sub GND			• Ground pin. Grounded as with pins 19 and 36.
2	V _{OUT}			• V-phase output pin.
3	W _{OUT}			• W-phase output pin.
4	AGC			• AGC pin. Controls hall-effect amplifier gain in response to hall-effect input frequency.

Truth Table

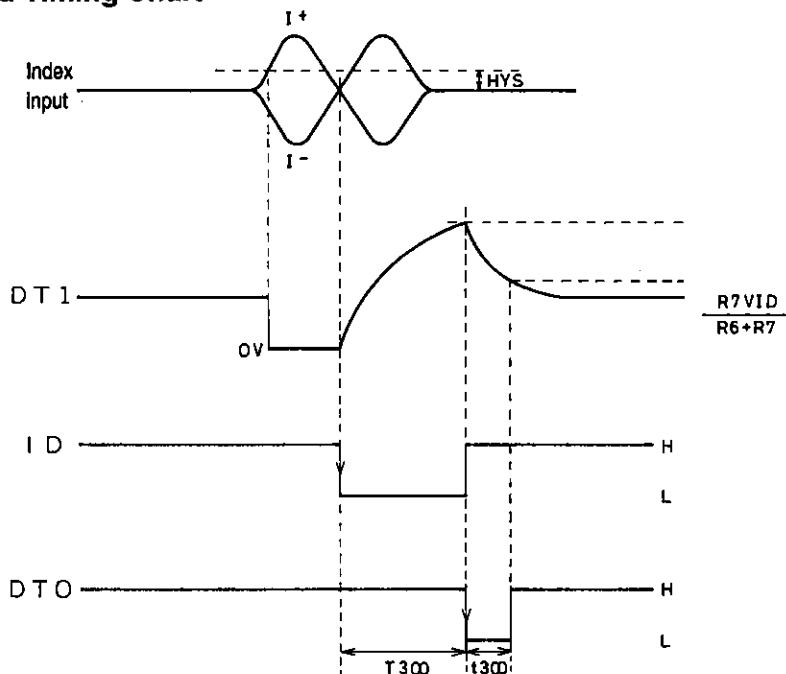
\	Source → Sink	Hall-Effect Input		
		U	V	W
1	V-phase → W-phase	H	H	L
2	V-phase → U-phase	L	H	L
3	W-phase → U-phase	L	H	H
4	W-phase → V-phase	L	L	H
5	U-phase → V-phase	H	L	H
6	U-phase → W-phase	H	L	L

When an "H" level exists for hall-effect input,

$$U^+ > U^-$$

$$V^+ > V^-$$

$$W^+ > W^-$$

Index and Timing Chart

When SL equals an "H" level,

$$\bullet T' \approx 0.693CR_6$$

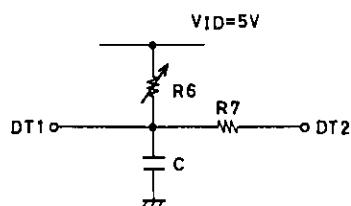
$$\bullet t' \approx \frac{CR_6R_7}{R_6 + R_7} \left\{ 0.405 + \ln \left(\frac{R_6 - R_7}{R_6 - 2R_7} \right) \right\}$$

When SL equals an "L" level,

$$\bullet T' \approx 0.577CR_6$$

$$\bullet t' \approx \frac{CR_6R_7}{R_6 + R_7} \left\{ 0.522 + \ln \left(\frac{0.781R_6 - R_7}{R_6 - 2R_7} \right) \right\}$$

Using only the ID pulse involves shorting DT1 and DT2.



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